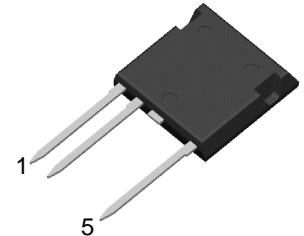
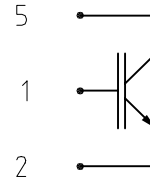


High Voltage IGBT

in High Voltage
ISOPLUS i4-PAC™

IXLF 19N220A
IXLF 19N250A

$I_{C25} = 32 \text{ A}$
 $V_{CES} = 2200/2500 \text{ V}$
 $V_{CE(sat)} = 3.2 \text{ V}$
 $t_f = 50 \text{ ns}$



IGBT			
Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	IXLF 19N220A	2200 V
		IXLF 19N250A	2500 V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^\circ\text{C}$		32 A
	$T_C = 90^\circ\text{C}$		19 A
I_{CM}	$V_{GE} = \pm 15 \text{ V}; R_G = 47 \Omega; T_{VJ} = 125^\circ\text{C}$		70 A
V_{CEK}	RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$		1200 V
P_{tot}	$T_C = 25^\circ\text{C}$		250 W

Features

- High Voltage IGBT
 - substitute for high voltage MOSFETs with significantly lower voltage drop and comparable switching speed
 - substitute for high voltage thyristors with voltage control of turn on and turn off
 - substitute for electromechanical trigger and discharge relays
- ISOPLUS i4-PAC™ high voltage package
 - isolated back surface
 - enlarged creepage towards heatsink
 - enlarged creepage between high voltage pins
 - application friendly pinout
 - high reliability
 - industry standard outline

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 19 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		3.2 4.7	3.9 V V	
$V_{GE(th)}$	$I_C = 1 \text{ mA}; V_{GE} = V_{CE}$	5		8 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.2	0.15 mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			500 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 1500 \text{ V}; I_C = 19 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 47 \Omega$		200 100 600 50 11 3.6	ns ns ns ns mJ mJ	
C_{ies}		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		2.2	nF
Q_{Gon}		$V_{CE} = 800 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 19 \text{ A}$		130	nC
R_{thJC}					0.5 K/W

Applications

- switched mode power supplies
- DC-DC converters
- resonant converters
- laser generators, x ray generators
- discharge circuits

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
F_c	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s, d_A	C pin - E pin	7.0		mm
d_s, d_A	pin - backside metal	5.5		mm
R_{thCH}	with heatsink compound		0.15	K/W
Weight			9	g

Dimensions in mm (1 mm = 0.0394")

